Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameters)
PART NUMBER: SSM3K7002FU
MANUFACTURER: TOSHIBA
Body Diode (Model Parameters) / ESD Protection

Bee Technologies Inc.

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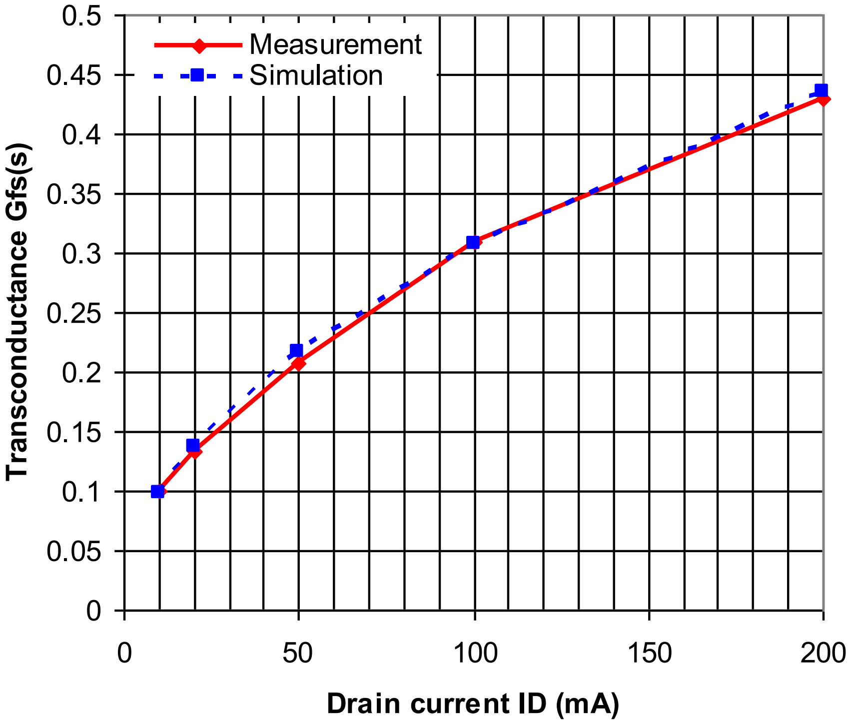
MOSFET MODEL PARAMETERS

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

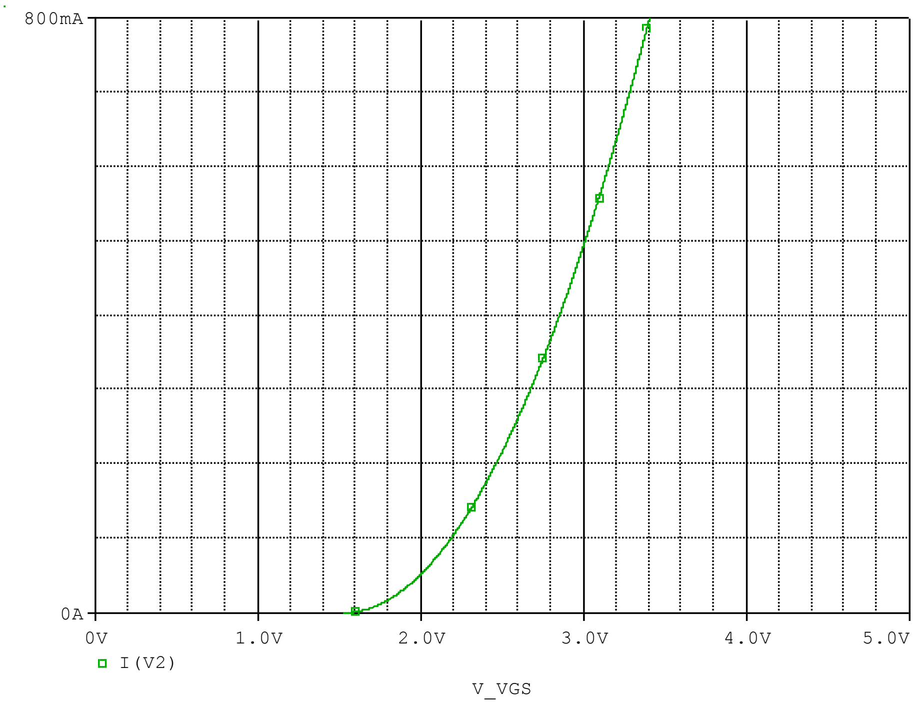


Comparison table

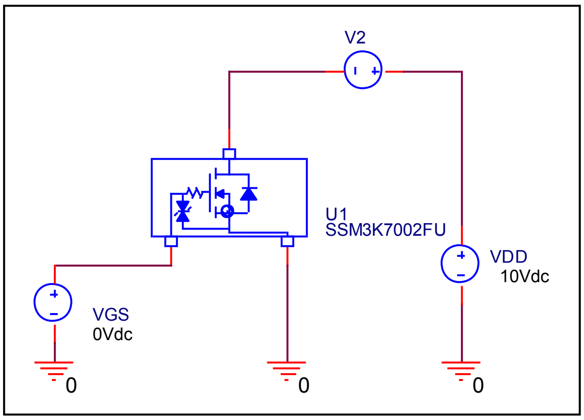
Id(mA)	Gfs(S)		Error(%)
	Measurement	Simulation	
10	0.1	0.098039216	-1.96
20	0.133	0.137931034	3.71
50	0.208	0.217391304	4.52
100	0.31	0.307692308	-0.74
200	0.43	0.434782609	1.11

Vgs-Id Characteristic

Circuit Simulation result

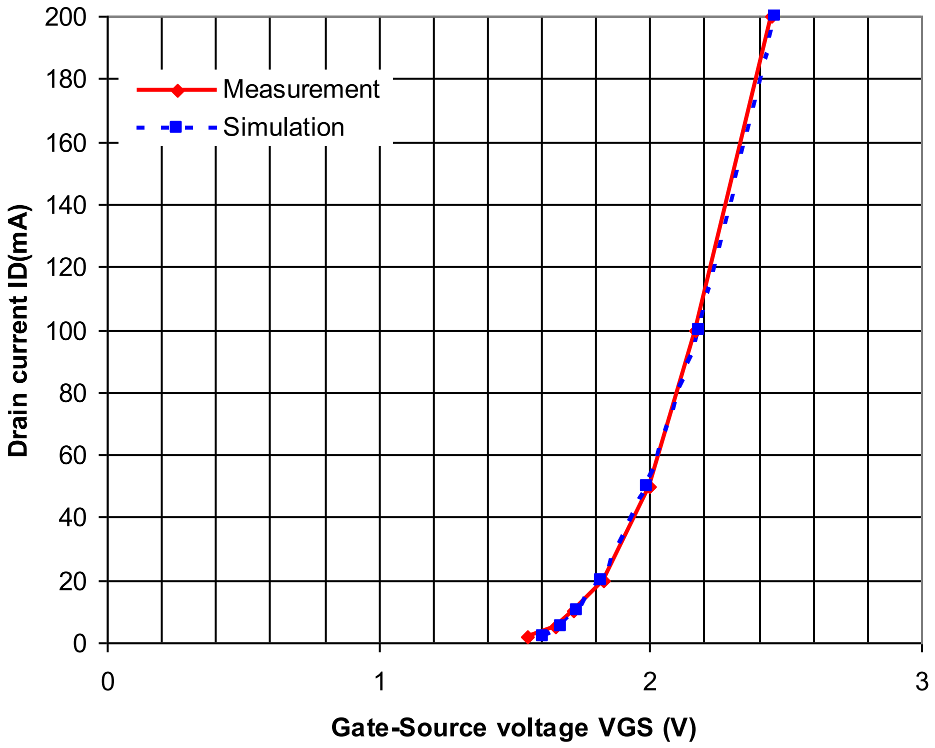


Evaluation circuit



Comparison Graph

Circuit Simulation Result

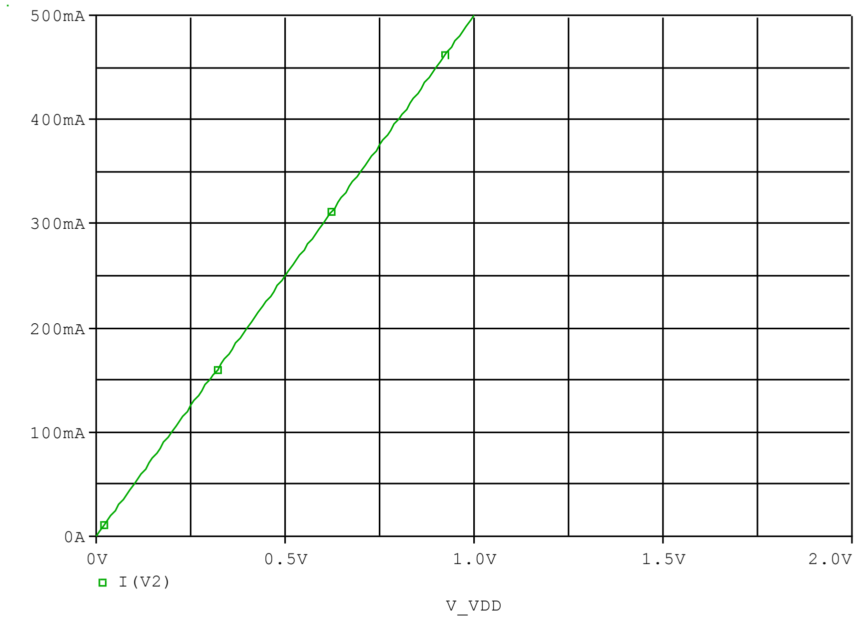


Simulation Result

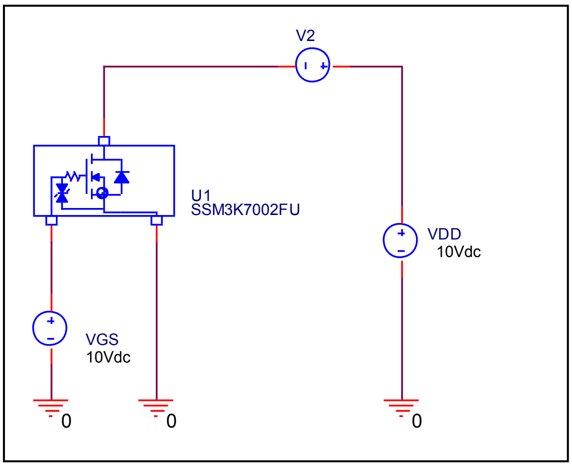
I_D(mA)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
2	1.55	1.61	3.87
5	1.65	1.67	1.21
10	1.72	1.73	0.58
20	1.83	1.82	-0.55
50	2.00	1.99	-0.50
100	2.17	2.18	0.46
200	2.45	2.46	0.41

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

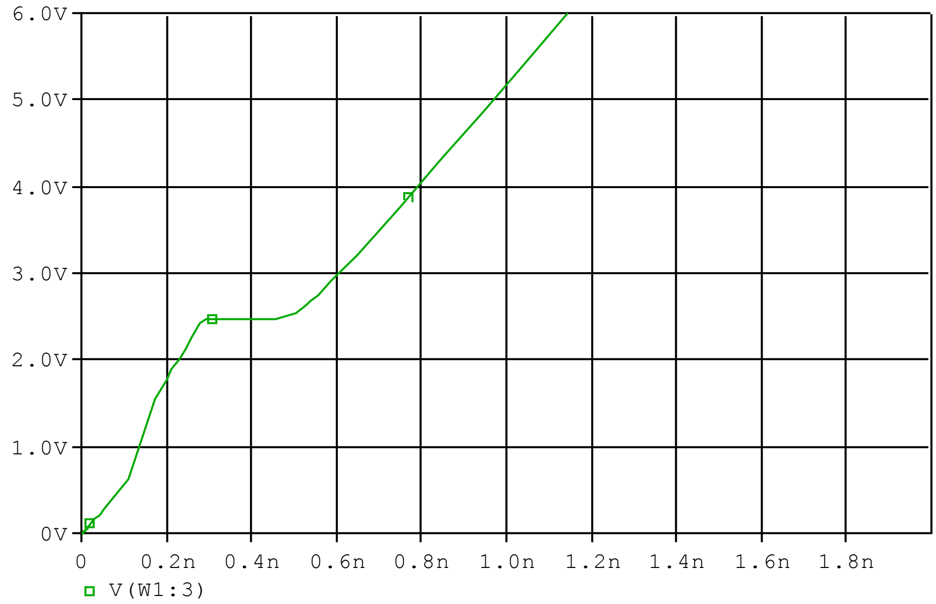


Simulation Result

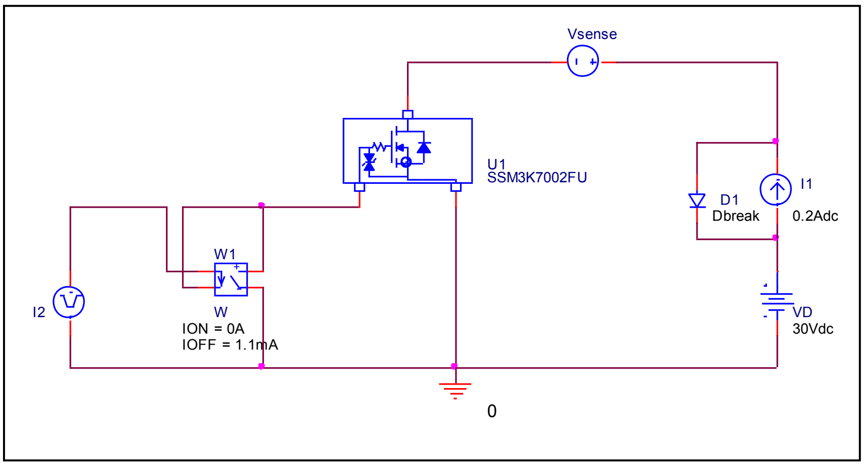
I_D=500mA, V_{GS}=10V	Measurement		Simulation		Error (%)
R_{DS} (on)	2.0	Ω	2.0	Ω	0.0

Gate Charge Characteristic

Circuit Simulation result



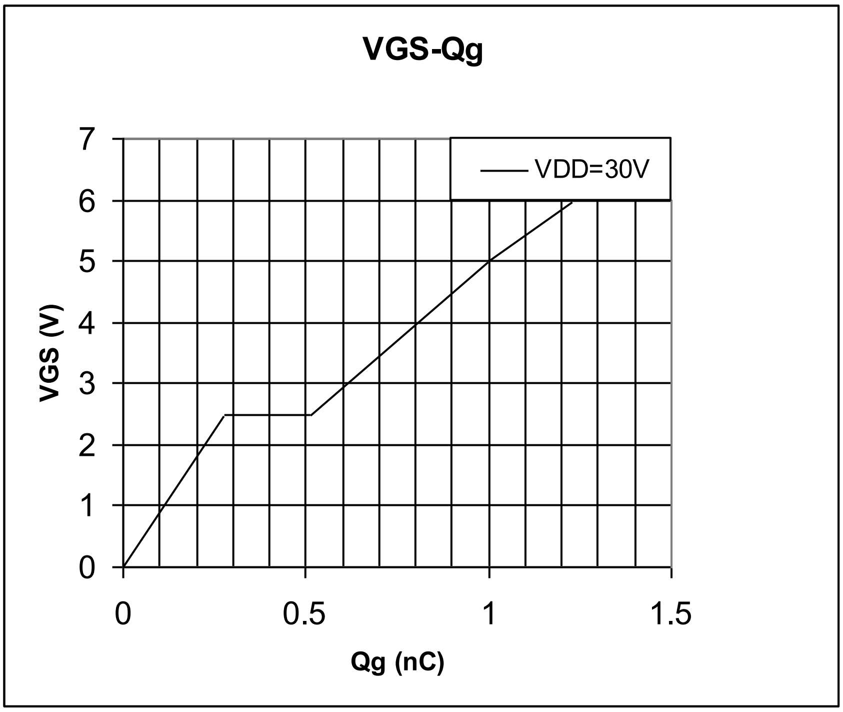
Evaluation circuit



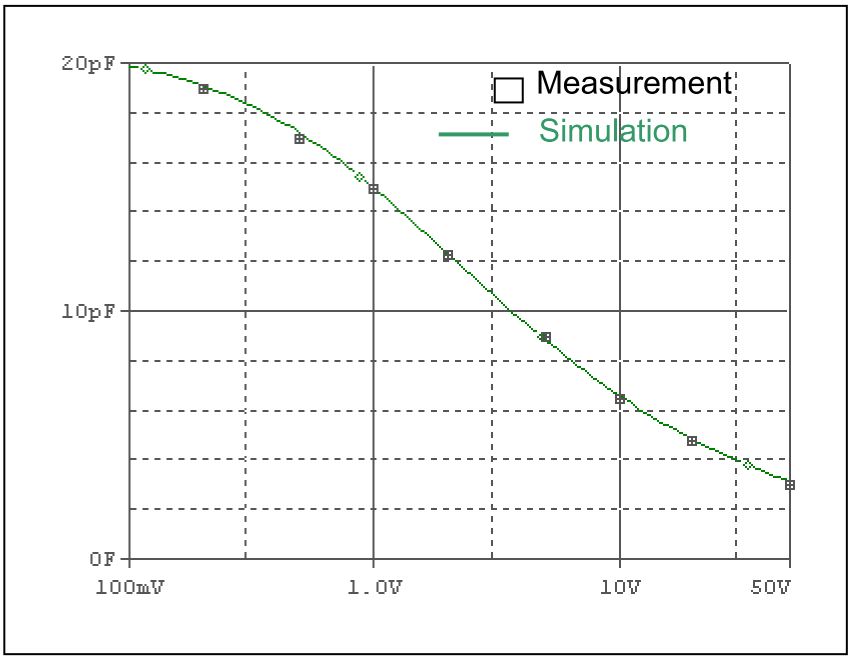
Simulation Result

V_{DD}=30V, I_D= 200mA ,V_{GS}=5V	Measurement		Simulation		Error (%)
Qgs	0.280	nC	0.286	nC	2.14
Qgd	0.236	nC	0.230	nC	-2.54

Gate Charge Characteristic Reference



Capacitance Characteristic

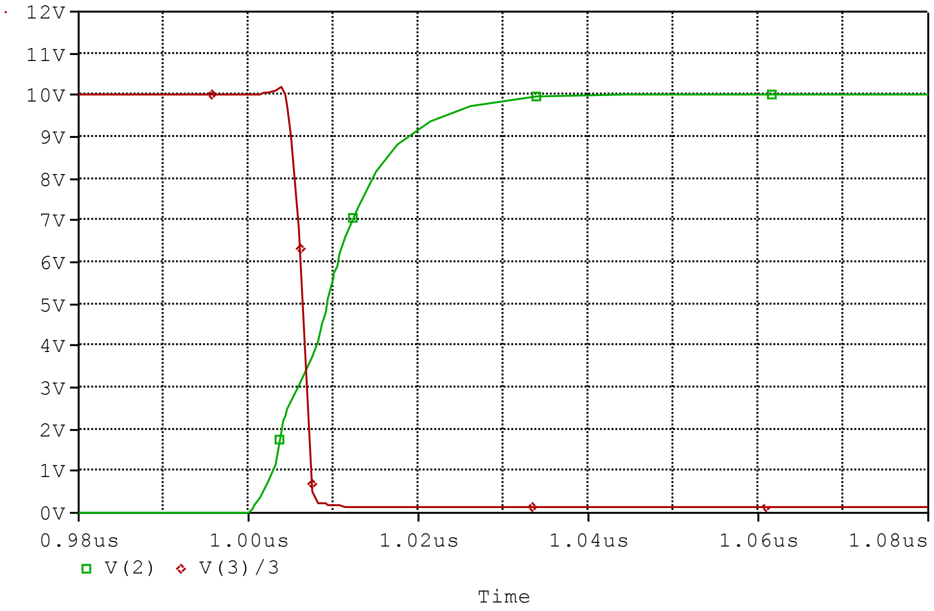


Simulation Result

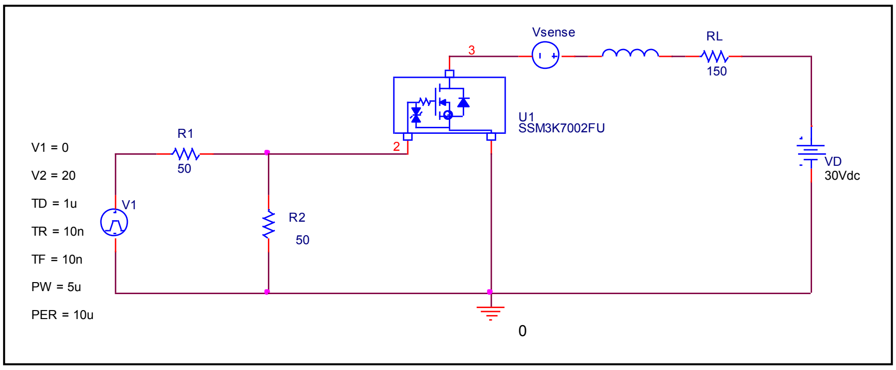
V_{DS}(V)	Cbd(pF)		Error(%)
	Measurement	**Simulation**	
0.1	20	19.87	-0.65
0.2	19	19.07	0.37
0.5	17	17.15	0.88
1	15	14.946	-0.36
2	12.3	12.315	0.12
5	8.8	8.82	0.23
10	6.5	6.58	1.23
20	4.8	4.815	0.31
50	3.1	3.15	1.61

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

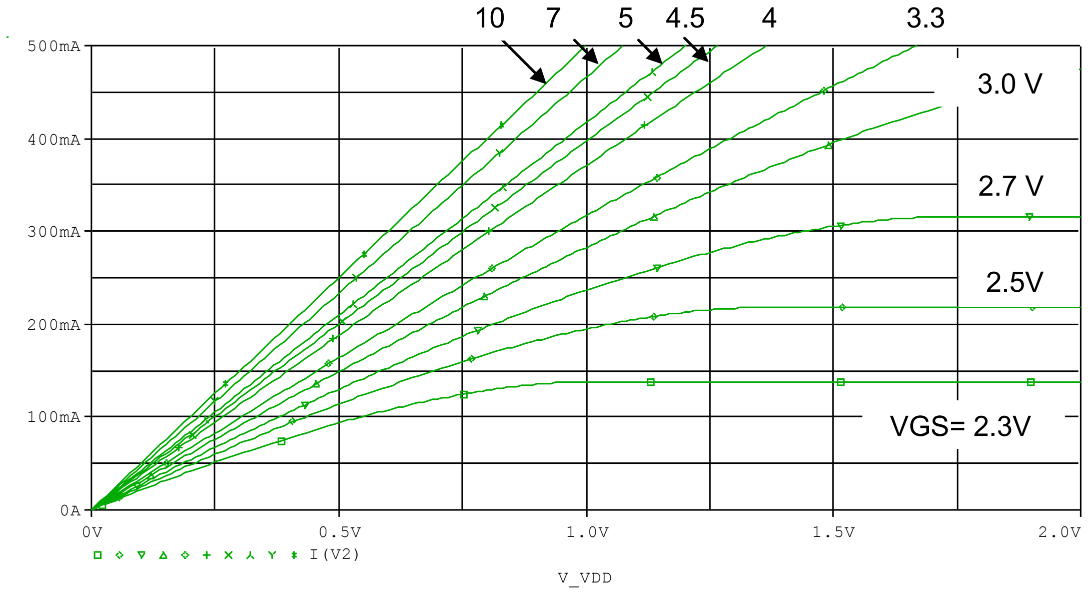


Simulation Result

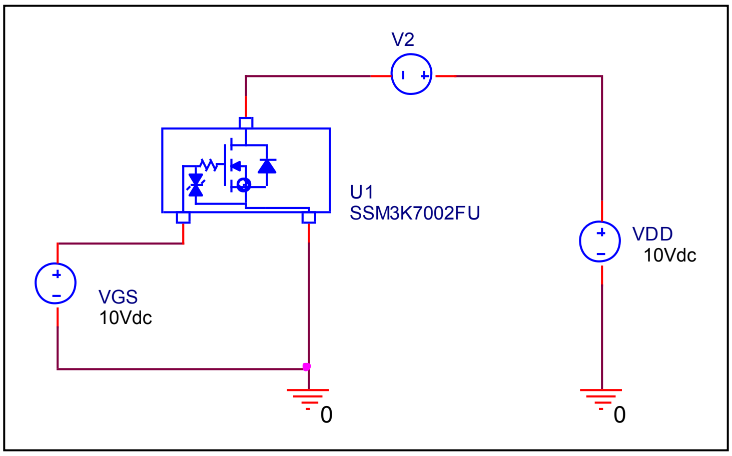
I_D=0.2A, V_{DD}= 30V, V_{GS}=0/10V	Measurement		Simulation		Error(%)
Td(on)	2.400	ns	2.418	ns	0.75

Output Characteristic

Circuit Simulation result

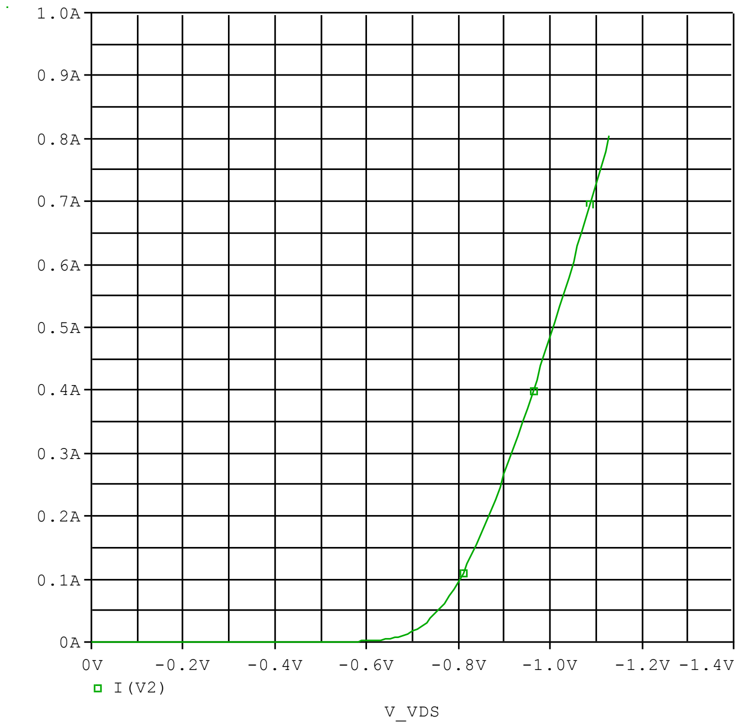


Evaluation circuit

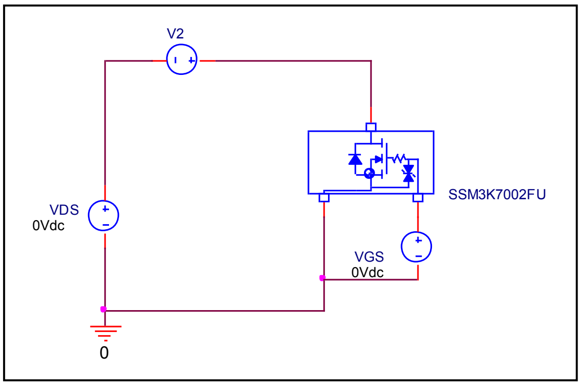


BODY DIODE SPICE MODEL
Forward Current Characteristic

Circuit Simulation Result

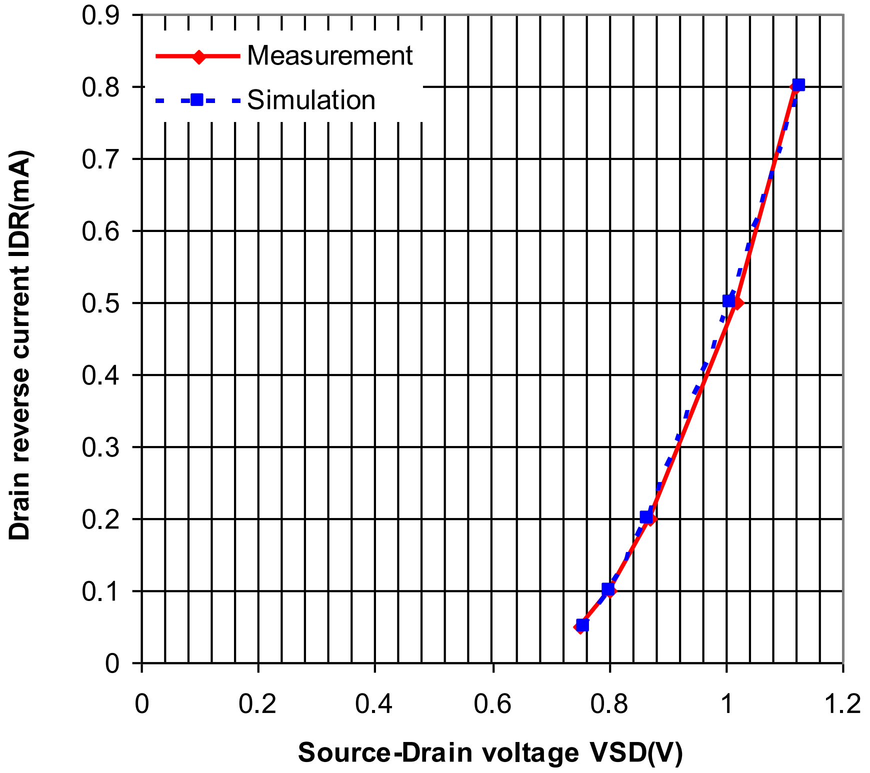


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

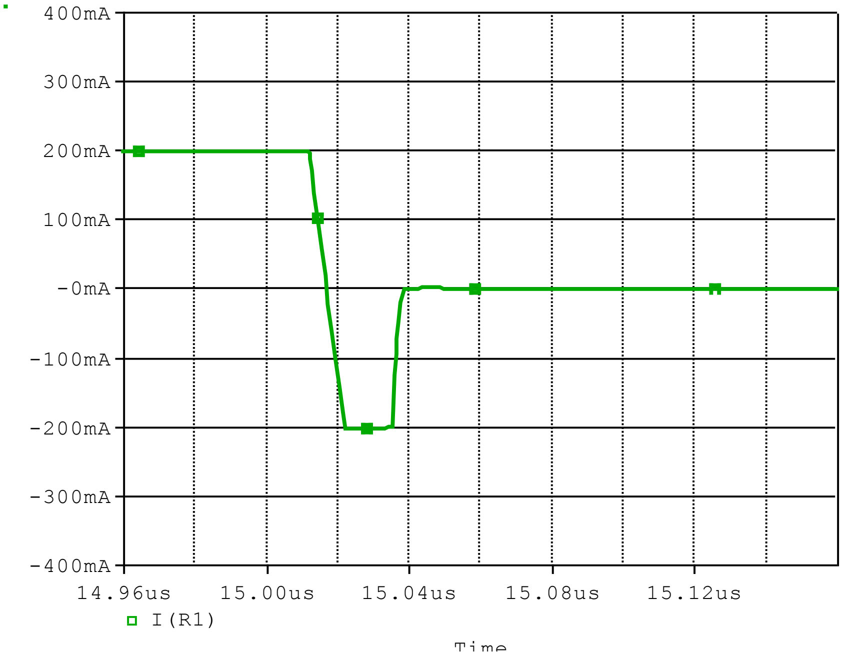


Simulation Result

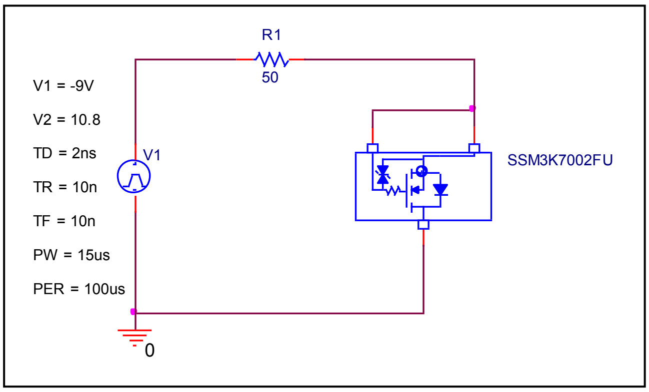
IDR(A)	VSD(V)		%Error
	Measurement	Simulation	
0.05	0.75	0.757	0.93
0.1	0.8	0.803	0.38
0.2	0.87	0.866	-0.46
0.5	1.02	1.007	-1.27
0.8	1.12	1.129	0.80

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

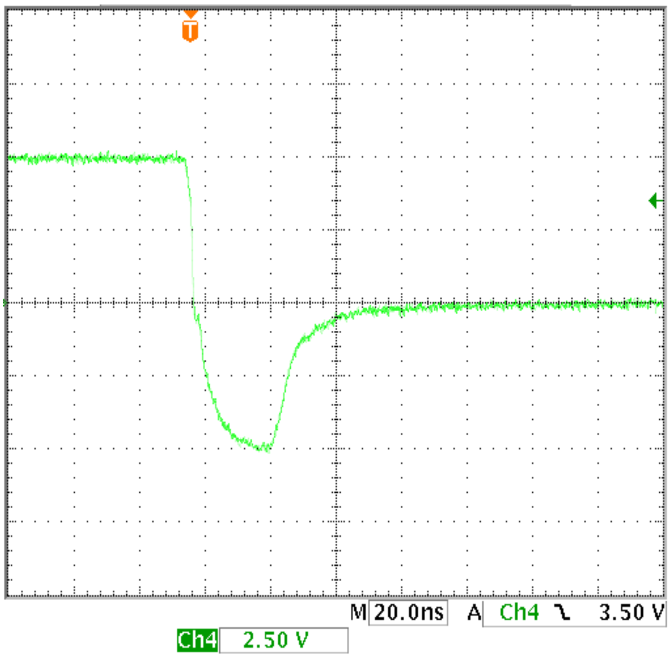


Compare Measurement vs. Simulation

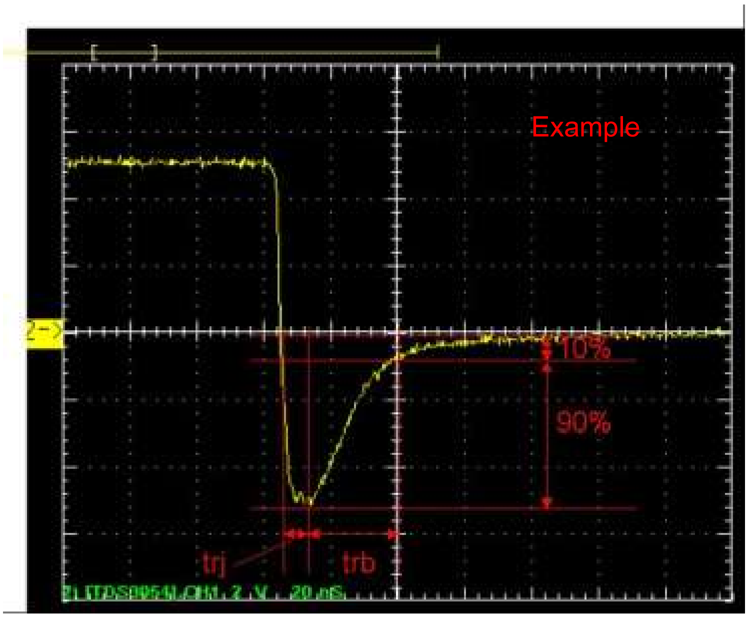
	Measurement		**Simulation**		**Error (%)**
trj	**17.000**	**ns**	**16.947**	**ns**	**-0.31176**
trb	**24.000**	**ns**	**3.9564**	**ns**	**-83.515**
trr	**41.000**	**ns**	**20.9034**	**ns**	**-49.0161**

Reverse Recovery Characteristic

Reference



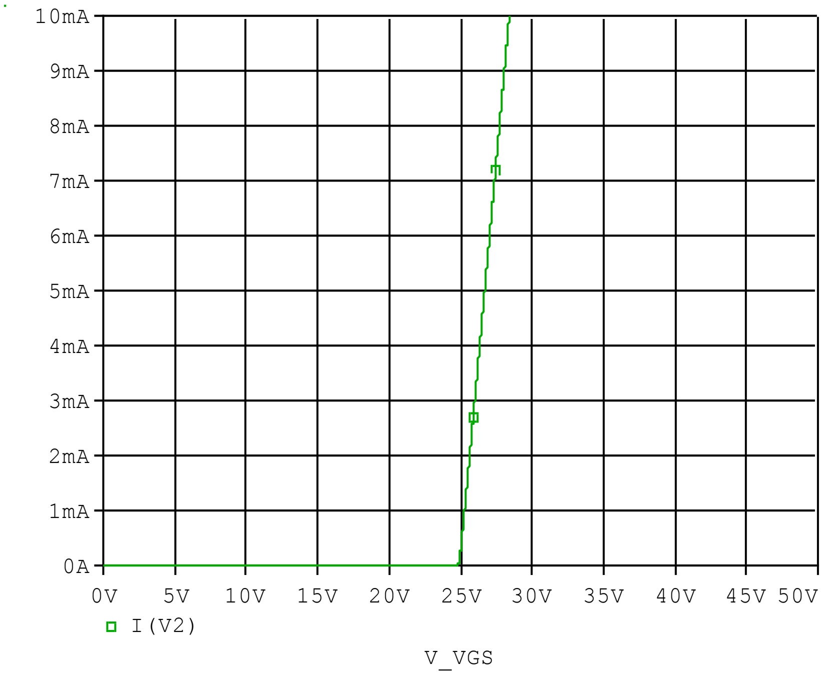
Trj=17 (ns)
Trb=24(ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



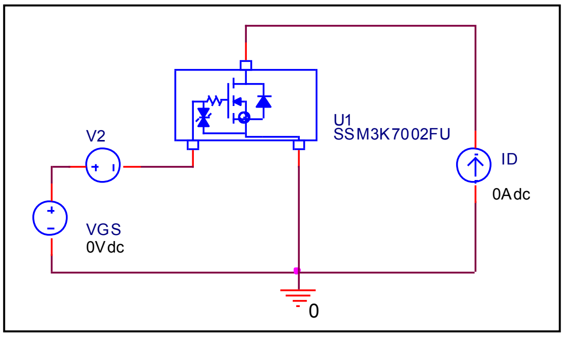
Relation between trj and trb

ESD PROTECTION DIODE SPICE MODEL
Zener Voltage Characteristic

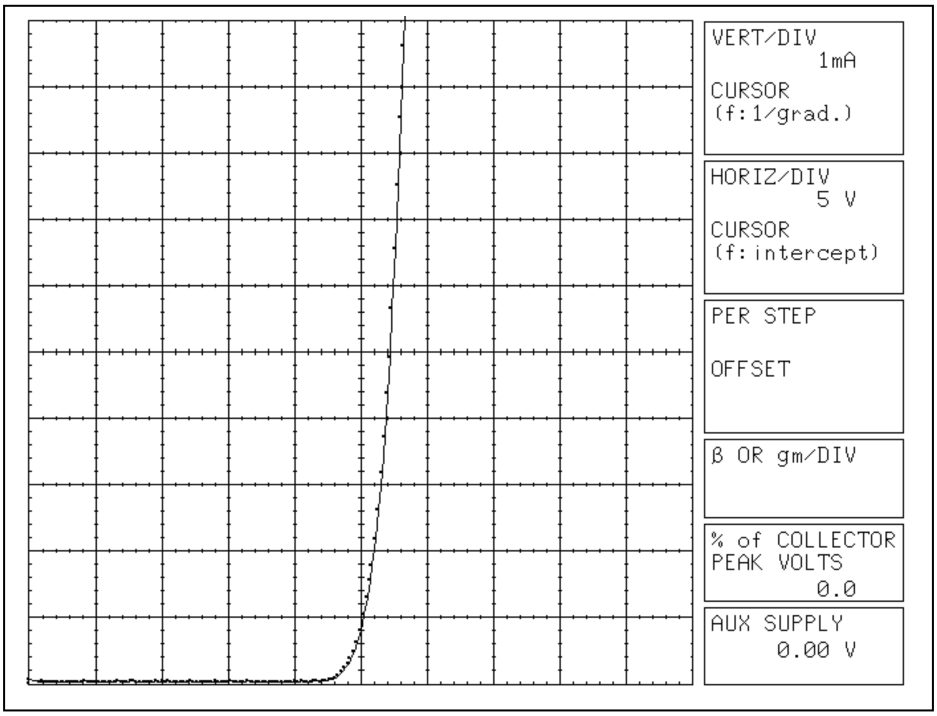
Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic Reference



VERT/DIV
1mA
CURSOR
(f:1/grad.)

HORIZ/DIV
5 V
CURSOR
(f:intercept)

PER STEP

OFFSET

β OR gm/DIV

% of COLLECTOR
PEAK VOLTS
0.0

AUX SUPPLY
0.00 V